

Vishay Semiconductors

Silicon PIN Photodiode



VBPW34FAS and VBPW34FASR are high speed and high sensitive PIN photodiodes. It is a surface mount device

(SMD) including the chip with a 7.5 mm² sensitive area and a daylight blocking filter matched with IR emitters operating at wavelength 870 nm or 950 nm.

FEATURES

- Package type: surface mount
- Package form: GW, RGW
- Dimensions (L x W x H in mm): 6.4 x 3.9 x 1.2
- Radiant sensitive area (in mm²): 7.5
- High radiant sensitivity
- Daylight blocking filter matched with 870 nm to 950 nm emitters
- Fast response times
- Angle of half sensitivity: $\phi = \pm 65^{\circ}$
- Floor life: 168 h, MSL 3, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

APPLICATIONS

- High speed detector for infrared radiation
- Infrared remote control and free air data transmissionsystems, e.g. in combination with TSFFxxxx series IR emitters

PRODUCT SUMMARY				
COMPONENT	I _{ra} (μA)	φ (deg)	λ _{0.5} (nm)	
VBPW34FAS	55	± 65	780 to 1050	
VBPW34FASR	55	± 65	780 to 1050	

Note

· Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING REMARKS PACKA		PACKAGE FORM	
VBPW34FAS	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Gullwing	
VBPW34FASR	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Reverse gullwing	

Note

• MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V _R	60	V
Power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	Pv	215	mW
Junction temperature		Tj	100	°C
Operating temperature range		T _{amb}	- 40 to + 100	°C
Storage temperature range		T _{stg}	- 40 to + 100	°C
Soldering temperature	Acc. reflow sloder profile fig. 8	T _{sd}	260	°C
Thermal resistance junction/ambient		R _{thJA}	350	K/W



RoHS

COMPLIANT

Vishay Semiconductors

Silicon PIN Photodiode



PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 50 mA	V _F		1	1.3	V
Breakdown voltage	$I_{R} = 100 \ \mu A, E = 0$	V _(BR)	60			V
Reverse dark current	V _R = 10 V, E = 0	I _{ro}		2	30	nA
Diode capacitance	V _R = 0 V, f = 1 MHz, E = 0	CD		70		pF
	V _R = 3 V, f = 1 MHz, E = 0	CD		25	40	pF
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	Vo		350		mV
Temperature coefficient of Vo	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	TK _{Vo}		- 2.6		mV/K
Short circuit current	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm}$	I _k		50		μA
Temperature coefficient of Ik	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	TK _{lk}		0.1		%/K
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, \\ V_R = 5 \text{ V}$	I _{ra}	45	55		μΑ
Angle of half sensitivity		φ		± 65		deg
Wavelength of peak sensitivity		λρ		950		nm
Range of spectral bandwidth		λ _{0.5}		780 to 1050		nm
Noise equivalent power	$V_{R} = 10 \text{ V}, \lambda = 950 \text{ nm}$	NEP		4 x 10 ⁻¹⁴		W/√Hz
Rise time	$V_{R} = 10 \text{ V}, \text{R}_{L} = 1 \text{k}\Omega, \\ \lambda = 820 \text{ nm}$	tr		100		ns
Fall time	$V_{R} = 10 \text{ V}, \text{R}_{L} = 1 \text{k}\Omega,$ $\lambda = 820 \text{ nm}$	t _f		100		ns

BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

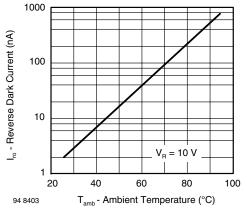


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

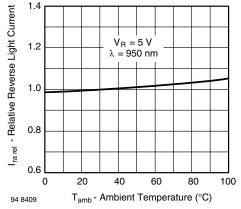


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature



Silicon PIN Photodiode

Vishay Semiconductors

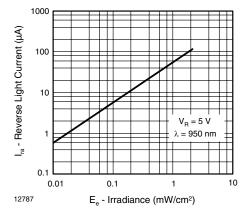


Fig. 3 - Reverse Light Current vs. Irradiance

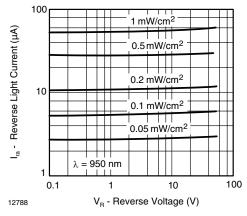


Fig. 4 - Reverse Light Current vs. Reverse Voltage

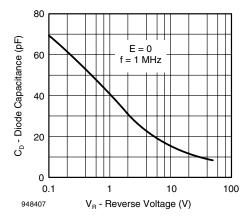


Fig. 5 - Diode Capacitance vs. Reverse Voltage

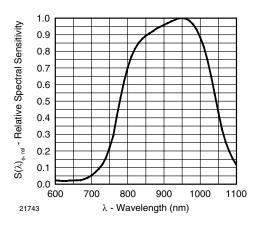


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

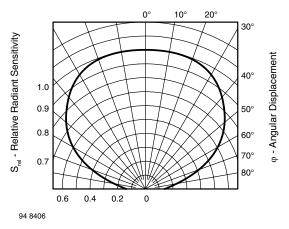


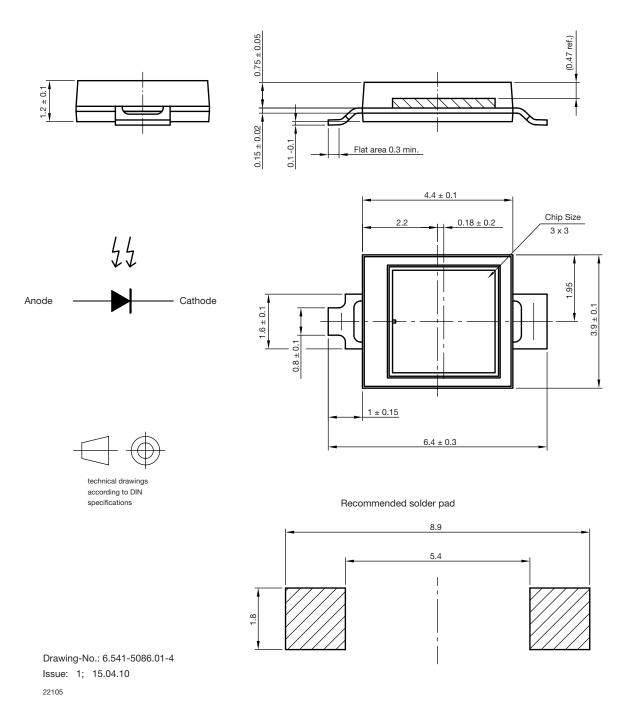
Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement

Vishay Semiconductors

Silicon PIN Photodiode



PACKAGE DIMENSIONS FOR VBPW34FAS in millimeters

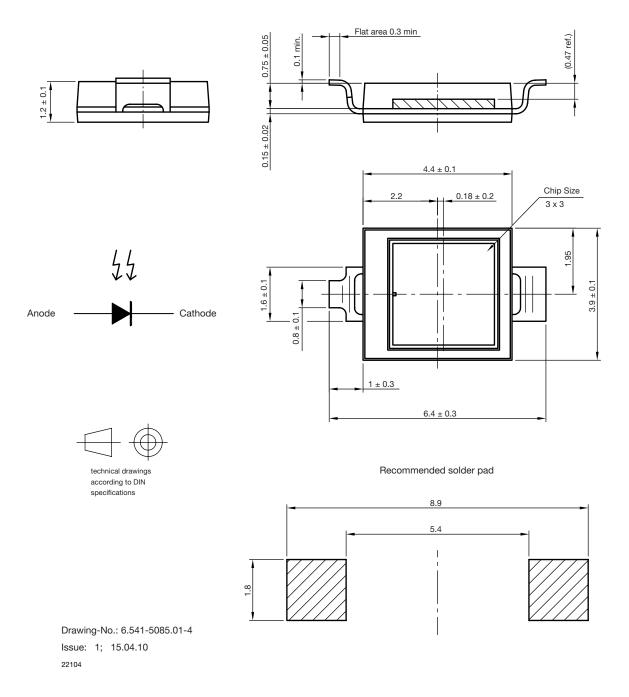




Silicon PIN Photodiode

Vishay Semiconductors

PACKAGE DIMENSIONS FOR VBPW34FASR in millimeters

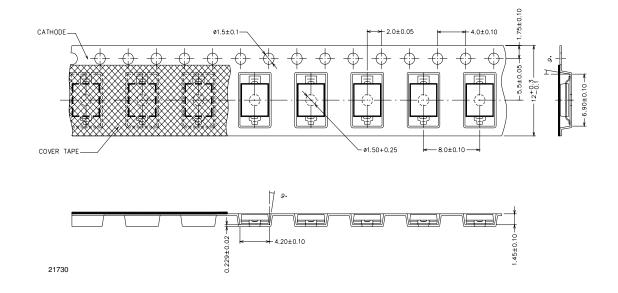


Vishay Semiconductors

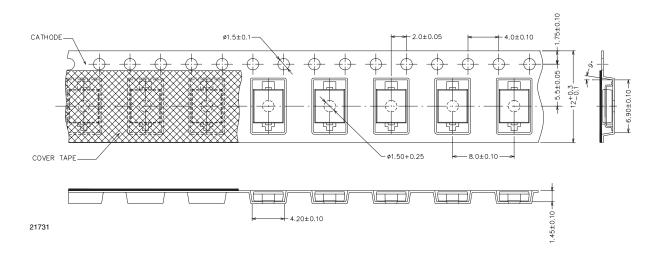
Silicon PIN Photodiode



TAPING DIMENSIONS FOR VBPW34FAS in millimeters



TAPING DIMENSIONS FOR VBPW34FASR in millimeters

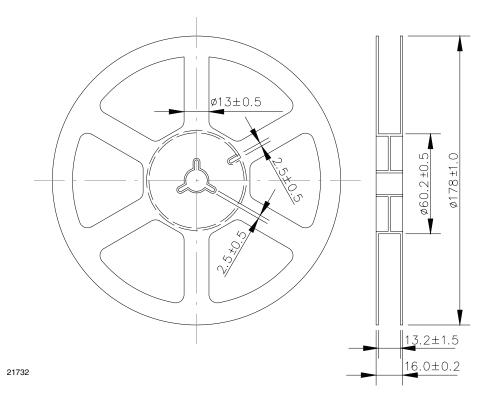




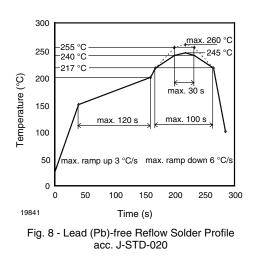
Silicon PIN Photodiode

Vishay Semiconductors

REEL DIMENSIONS FOR VBPW34FAS AND VBPW34FASR in millimeters



SOLDER PROFILE



DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020: Moisture sensitivity: level 3 Floor life: 168 h Conditions: $T_{amb} < 30$ °C, RH < 60 %

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or recommended conditions: 192 h at 40 °C (+ 5 °C), RH < 5 % or 96 h at 60 °C (+ 5 °C), RH < 5 %.

Document Number: 81127 Rev. 1.1, 20-Apr-10



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.